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FISH & RICHARDSON P.C. 11.8.02004

Attorney's Docket No.: 07977-088002/US3155D1

# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: H. Zhang Serial No.: 09/362,808 Art Unit : 2814 Examiner : S. Rao

Filed

: July 28, 1999

Confirmation No. 7320

Title

: METHOD OF FABRICATING SEMICONDUCTOR DEVICE

#### BOX RCE

Commissioner for Patents Washington, D.C. 20231

### AMENDMENT

Sir:

Please amend the above-referenced application as follows.

# In the Claims:

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Please amend the claims as follows.

**TECHNOLOGY CENTER 2800** 

1. (Amended) A semiconductor device comprising:

a semiconductor having at least channel, source and drain regions;

an insulating film formed on said semiconductor;

a gate electrode over the insulating film;

a first interlayer insulating film over said insulating film and the gate electrode;

### CERTIFICATE OF TRANSMISSION BY FACSIMILE

I hereby certify that this correspondence is being transmitted by facsimile to the Patent and Trademark Office on the date indicated below.

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